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(54) **METHOD FOR FORMING A PATTERNED SEMICONDUCTOR FILM**

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(57) **ABSTRACT**

A process for forming a pattern in a semiconductor film is provided. The process comprises the steps of: providing a substrate; providing an organic semiconductor film adjacent the substrate; and providing a destructive agent adjacent selected portions of the organic semiconductor film, the destructive agent changing a property of selected portions of the organic semiconductor film substantially through the full thickness of the organic semiconductor film such that the property of the selected portions of the organic semiconductor film differs from the property of remaining portions of the organic semiconductor film. A method for manufacturing a transistor comprises the steps of: providing a substrate; providing a gate electrode adjacent the substrate; providing a gate dielectric adjacent the substrate and the gate electrode; providing a source electrode and a drain electrode adjacent the gate dielectric; providing a mask adjacent the gate dielectric in a pattern such that the source electrode, the drain electrode, and a portion of the gate dielectric remain exposed; and providing a semiconductor layer comprising one of an organic semiconductor and a plurality of inorganic colloidal particles, adjacent the source electrode, the drain electrode, the portion of the gate dielectric and the mask, thereby forming the transistor, the semiconductor layer having a thickness less than a thickness of the mask.

26 Claims, 5 Drawing Sheets